



Attorney Doc  
33035M132

P A T E N T

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants : Jun-ichi Hashimoto, et al.  
Serial No. : 10/667,142 Art Unit : Not Yet Assigned  
Filed : September 22, 2003 Examiner : Not Yet Assigned  
For : SEMICONDUCTOR OPTICAL DEVICE

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure under 37 C.F.R. §1.56, Applicants enclose an Information Disclosure Citation Form (PTO-1449). Copies of the cited documents are enclosed. The documents cited hereby are those identified and discussed on pages 1 and 2 of Applicants' specification.

It is respectfully requested that the cited documents be considered by the Examiner in the above-identified patent application and that the cited documents be made officially of record therein. It is further requested that a listing of the same appear on the face of any patent which may issue from this application.

This Information Disclosure Statement is being filed within three (3) months of the filing date of the application. Therefore, it is believed that no fees are due under 37 C.F.R. Section 1.97(b)(3).


Respectfully submitted,  
SMITH, GAMBRELL & RUSSELL, LLP



October 17, 2003

By :

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FORM PTO-1449	ATTY. DOCKET <b>33035M132</b>	SERIAL NO. 10/667,142
<b>INFORMATION DISCLOSURE STATEMENT</b> 	APPLICANT: Jun-ichi Hashimoto, et al.	
	FILING DATE September 22, 2003	GROUP ART UNIT To Be Assigned

### U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE, IF APPROPRIATE
	AA						
	AB						

### FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO	
	AC							
	AD							

### OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

	AE	H. Nishi, et al., "Self-Aligned Structure InGaAsP/InP DH Lasers", Appl. Phys. Lett. 35(3), 1 August 1979, pp. 232-234
	AF	Ronald J. Nelson, et al., "CW Electrooptical Properties of InGaAsP ( $\lambda = 1.3 \mu\text{m}$ ) Buried-Heterostructure Lasers", IEEE Journal of Quantum Electronics, Vol. QE-17, No. 2, February 1981, pp. 202-207
	AG	
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EXAMINER:		DATE CONSIDERED:
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>		